

Description

The SX3415MI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = -20V$ $I_D = -4.5A$

$R_{DS(ON)} < 40m\Omega$ @ $V_{GS}=4.5V$

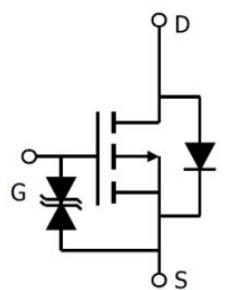
ESD=2500V HBM

Application

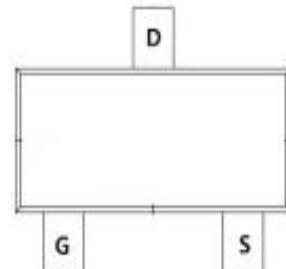
Battery protection

Load switch

Uninterruptible power supply



SOT-23-3L

**Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)**

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-4.5	A
$I_D @ T_c=70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-3.0	A
IDM	Pulsed Drain Current ²	-17	A
$P_D @ T_c=25^\circ C$	Total Power Dissipation ³	1.1	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	125	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	110	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D = -250\mu\text{A}$	-20	-	-	V
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = -20\text{V}, V_{GS} = 0\text{V}$,	-	-	-1	μA
IGSS	Gate to Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 10\text{V}$	-	-	± 10	μA
VGS(th)	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-0.4	-0.7	-1.0	V
RDS(on)	Static Drain-Source on-Resistance	$V_{GS} = -4.5\text{V}, I_D = -4\text{A}$	-	31	40	$\text{m}\Omega$
		$V_{GS} = -2.5\text{V}, I_D = -3\text{A}$	-	40	56	
Ciss	Input Capacitance	$V_{DS} = -10\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$	-	289	-	pF
Coss	Output Capacitance		-	98	-	pF
Crss	Reverse Transfer Capacitance		-	22	-	pF
Qg	Total Gate Charge	$V_{DS} = -10\text{V}, I_D = -4.1\text{A}, V_{GS} = -4.5\text{V}$	-	9	-	nC
Qgs	Gate-Source Charge		-	1	-	nC
Qgd	Gate-Drain("Miller") Charge		-	2.6	-	nC
td(on)	Turn-on Delay Time	$V_{DD} = -10\text{V}, R_G = 1\Omega, V_{GEN} = -4.5\text{V}, R_L = 1.2\Omega$	-	12	-	ns
tr	Turn-on Rise Time		-	35	-	ns
td(off)	Turn-off Delay Time		-	30	-	ns
tf	Turn-off Fall Time		-	10	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	-4.1	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-16.4	A
VSD	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = -4.1\text{A}$	-	-	-1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

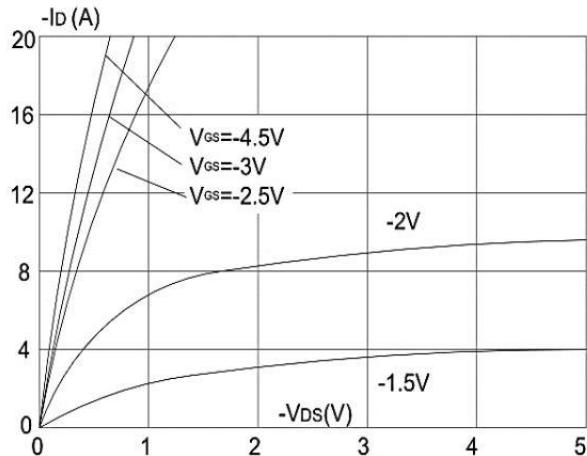


Figure 1: Output Characteristics

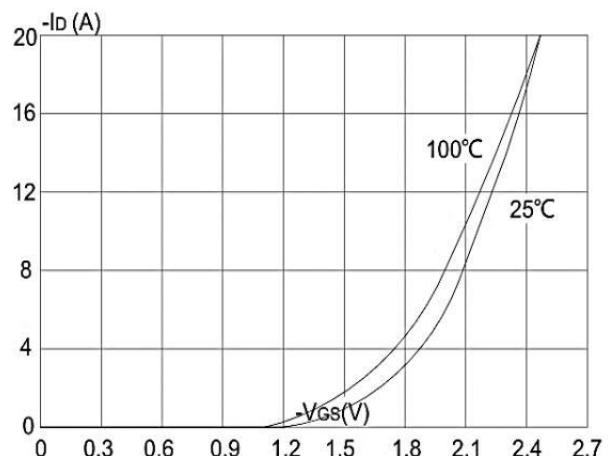


Figure 2: Typical Transfer Characteristics

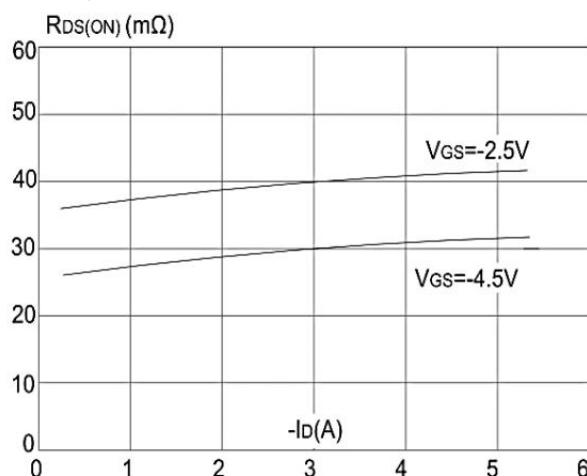


Figure 3: On-resistance vs. Drain Current

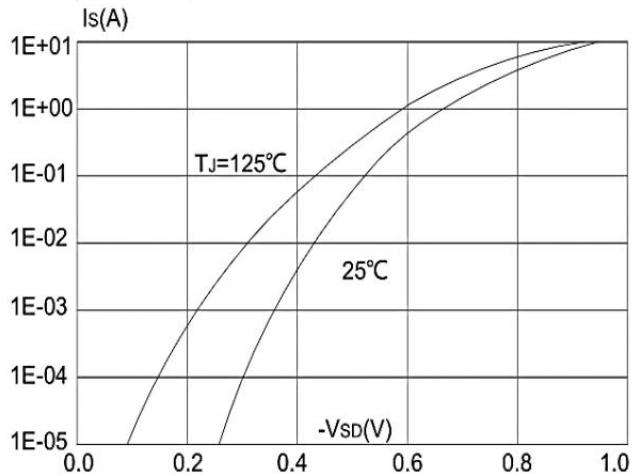


Figure 4: Body Diode Characteristics

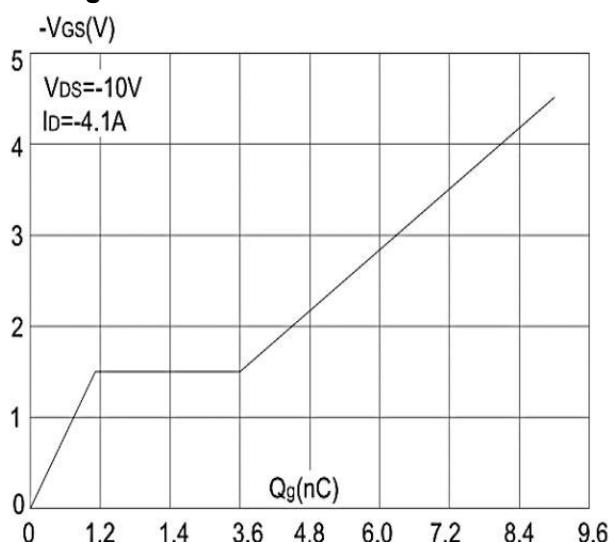


Figure 5: Gate Charge Characteristics

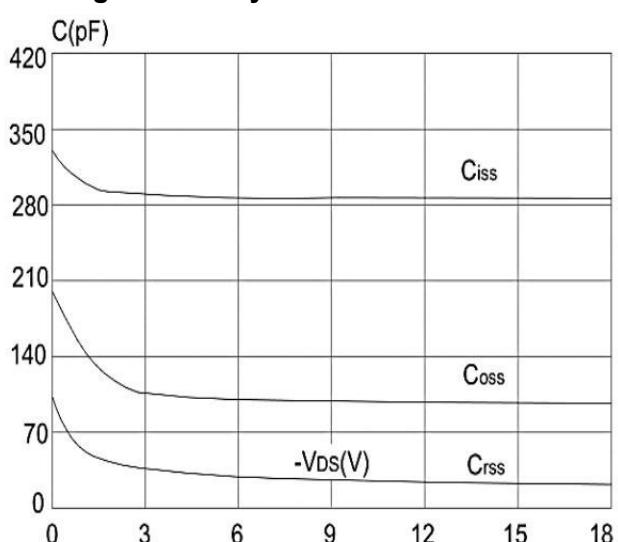


Figure 6: Capacitance Characteristics

Typical Characteristics

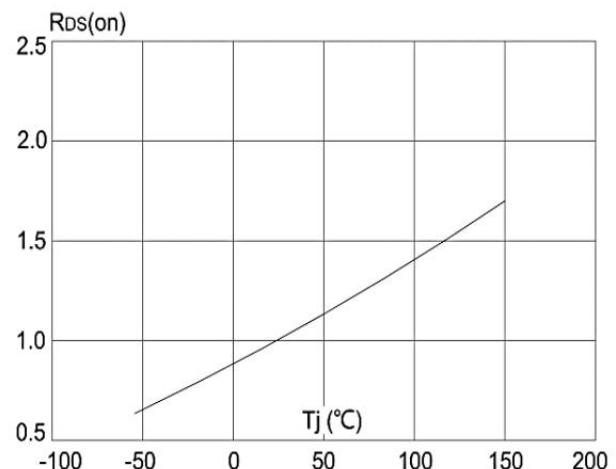
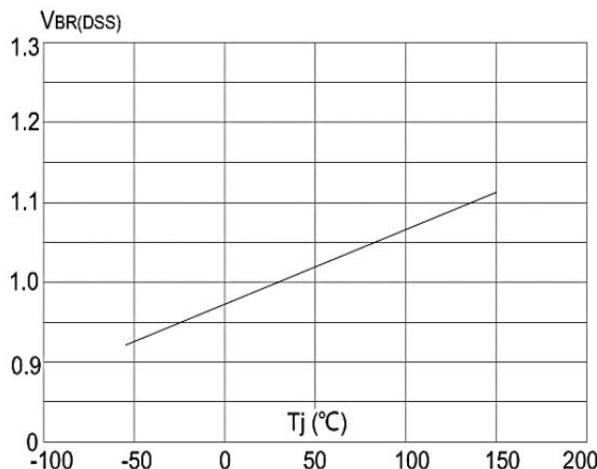


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

Figure 8: Normalized on Resistance vs. Junction Temperature

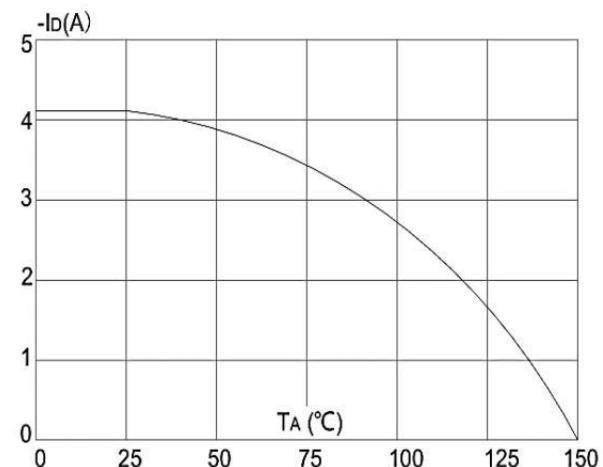
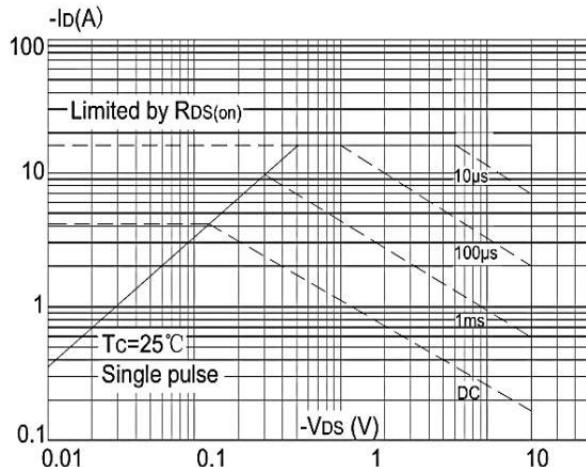


Figure 9: Maximum Safe Operating Area

Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

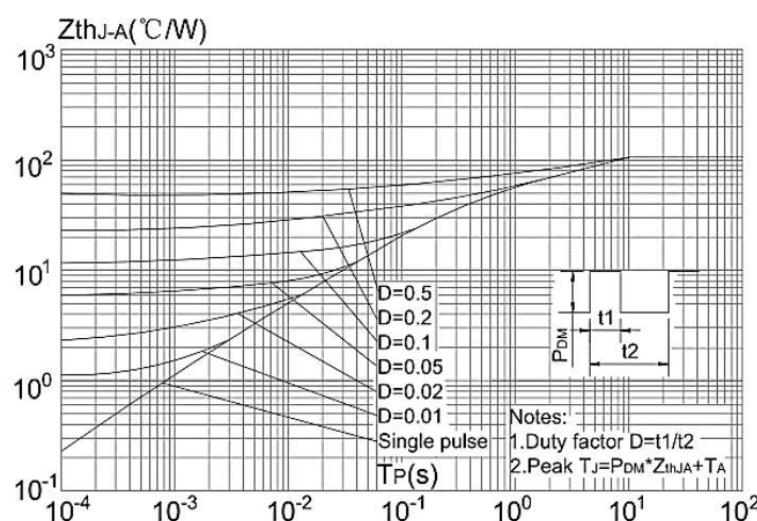
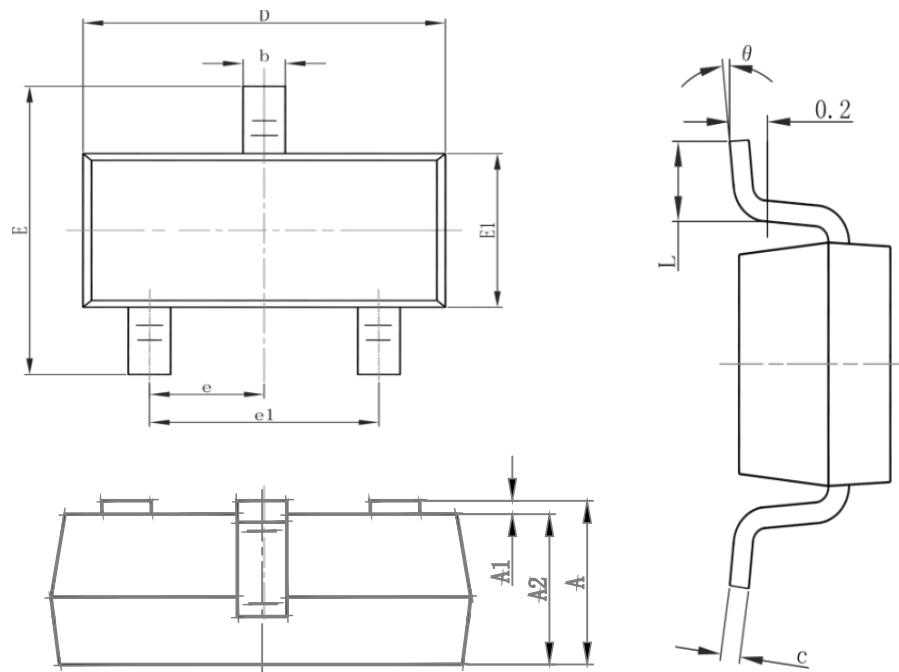


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

Package Mechanical Data-SOT23-3L Single



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT23-3L		3000